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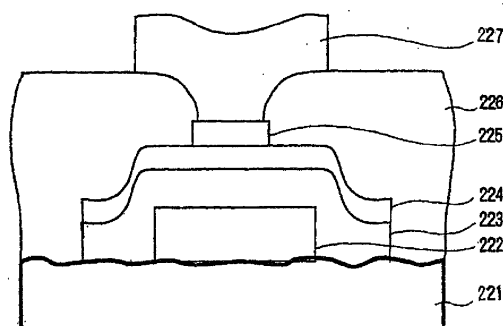
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This application was filed on 12.03.2008 as a
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(54) **Tunnel magnetoresistance element**

(57) A tunnel magnetoresistive element having a
structure in which a nonmagnetic single-crystal metal or
nonmagnetic highly-oriented-polycrystalline interlayer
lies between a barrier layer and a ferromagnetic elec-
trode.

FIG. 17



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